CHANGE OF ATTORNEY INFORMATION

The law firm of Helfgott and Karas, P.C. joined Rosenman & Colin LLP on September 1, 2001. The correspondence information for all current Helfgott & Karas files was changed with the USPTO by formal, electronic communication. This is to confirm that all future correspondence in this matter should be directed to Rosenman & Colin LLP, 575 Madison Avenue, New York, New York, 10022-2585, Phone: (212) 940-8800, Fax: (212) 940-8986/8987.

OBJECTIONS TO THE DRAWING AND SPECIFICATION

The drawing and specification are both objected to because reference numerals 118 and 1106 as shown in Figure 1 are not described in the specification. The specification is amended to identify reference numerals 118 and 1106 in association with the existing textual description for Figure 1. Accordingly, it is respectfully requested that the Examiner withdraw the objections to the drawing and specification.

REJECTIONS UNDER 35 U.S.C. § 102

The Manual of Patenting Examining Procedure (MPEP) § 2131 clearly sets forth the standard for rejecting a claim under 35 U.S.C. § 102(b). "A claim is anticipated only if each and every element as set forth in the claim is found, either expressly or inherently described, in a single prior art reference." (MPEP § 2131, quoting Verdegaal Bros. v. Union Oil Co. of California 2 USPQ2d 1051, 1053 (Fed Cir. 1987)). "The identical invention must be shown in as complete detail as is contained in the ...claim." (MPEP § 2131, quoting Richardson v. Suzuki Motor Co., 9 USPQ2d 1913, 1920 (Fed. Cir. 1989)).

"The elements must be arranged as required by the claim, but this is not an *ipsissimis verbis* test, i.e. identity of terminology is not required." (MPEP § 2131, citing In re Bond, 15 USPQ2d 1566 (Fed. Cir. 1990)).

A basic advantage of the present invention is that the first-property semiconductor region coexists with the second-property semiconductor region in the same film which is covered with the insulation film as shown in FIG. 12E and 21C. In the case of a large-area substrate, coexistence of the first-property and second-property semiconductor region in the same layer allows the time required for semiconductor reformation to be cut, resulting in improved throughput. For example, when channel, source, and drain regions of a TFT are formed in a crystallized semiconductor region, it is not necessary to change the regions used for alignment marks or pattern-check regions other than the TFT into a crystallized region. Accordingly, by selectively changing the second-property semiconductor film into the first-property semiconductor region, effective film structure formation can be achieved. There is no such motivation in the cited reference, Makita et al., U.S. Patent No. 5,821,562.

In Makita et al., there are four films: an amorphous film (column 30, lines 58-61); a crystalline film (column 31, lines 22-35); a doped film (column 32, lines 30-33); and an activated film (column 32, line 43-52). However, the amorphous film (corresponding to the second-property semiconductor film in the present claim 1) is not left in a final state.

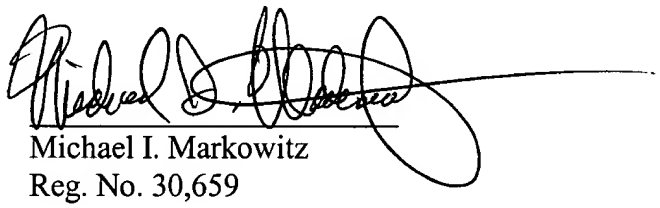
CONCLUSION

An earnest effort has been made to be fully responsive to the Examiner's objections. In view of the above amendments and remarks, it is believed that independent claims 1 and 7 and the claims dependent therefrom, are in condition for allowance. Passage of this case to allowance is earnestly solicited. However, if for any reason the Examiner should consider this application not to be in condition for allowance, he is respectfully requested to telephone the undersigned attorney at the number listed below prior to issuing a further Action.

Attached is a marked up version of the changes made to the specification and claims by the current amendment. The attached pages are captioned **"Version With Marks To Show Changes Made".**

Any fee due with this paper may be charged on Deposit Account 50-1290.

Respectfully submitted,



Michael I. Markowitz
Reg. No. 30,659

Enclosure: Version With Markings to Show Changes Made

ROSENMAN & COLIN, LLP
575 MADISON AVENUE
NEW YORK, NEW YORK 10022-2585
PHONE: (212) 940-8800
DOCKET NO.: NECK 17.552 (100806-17282)
CUSTOMER NUMBER 100806

VERSION WITH MARKS TO SHOW CHANGES MADE OF

AMENDED APPLICATION – S/N 09/614,286

IN THE SPECIFICATION

Fig. 1 is a schematic view showing one example of a structure of a pulse laser beam irradiator. A laser beam (1106) supplied form a pulse laser beam source (1101) reaches a silicon thin film (1107) on a glass substrate [(1109)] (118) as an irradiated object through an optical path defined by optical devices such as mirrors (1102, 1103, 1105) and a beam homogenizer (1104) installed for homogenizing a spatial intensity. Generally, since one irradiation range is small, a laser beam irradiation is carried out at a desired position on the glass substrate by moving the substrate on an x-y stage (1109). There is also a method of moving the optical devices or combining the optical devices with the stage instead of moving the x-y stage.

IN THE CLAIMS

1. **(Amended)** A method for forming a first-property semiconductor film at a desired position on a substrate, comprising the steps of:

a) preparing the substrate having a second-property semiconductor film formed thereon;

b) preparing an optical mask having a predetermined pattern;

c) relatively positioning a projection area of the optical mask at the desired position on the substrate;

d) irradiating the desired position of the second-property semiconductor film with laser light through the optical mask to change an irradiated portion of the second-property semiconductor film to the first-property semiconductor film; and

e) forming an insulation film on [at least the first-property semiconductor film.] the first-property semiconductor film and the second-property semiconductor film.

7. **(Amended)** A method for forming a crystalline semiconductor film at a desired position on a substrate, comprising the steps of:

a) preparing the substrate having an amorphous semiconductor film formed thereon;

b) preparing an optical mask having a predetermined pattern;

c) relatively positioning a projection area of the optical mask at the desired position on the substrate;

d) irradiating the desired position of the amorphous semiconductor film with laser light through the optical mask to change an irradiated portion of the amorphous semiconductor film to the crystalline semiconductor film; and

e) forming an insulation film on [at least the crystalline semiconductor film.] the crystalline semiconductor film and the amorphous semiconductor film.